HUASHUO SEMICONDUCTOR

HSBA3086

## N-Ch 30V Fast Switching MOSFETs

General Description

- 100% UIS Tested
- Advanced Trench Technology
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

Product Summary

V_{DS}	30	V
$R_{DS(ON),typ}$	0.7	mΩ
I_D	230	A

Applications

- Power Management in Desktop Computer
- DC/DC Converters

PRPAK5X6 Pin Configuration
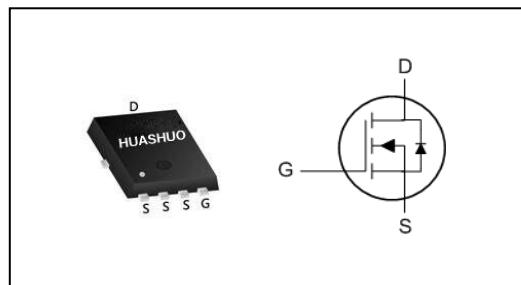
Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1,6]	230	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1,6]	147	A
I_{DM}	Pulsed Drain Current[2]	400	A
EAS	Single Pulse Avalanche Energy[3]	420	mJ
I_{AS}	Avalanche Current	41	A
P_D@T_C=25°C	Total Power Dissipation[4]	89	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.4	°C/W

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	0.7	0.9	mΩ
		V_{GS}=4.5V , I_D=20A	---	1.0	1.4	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.7	2.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃		---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.4	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=10V , I_D=20A	---	65	---	nC
Q_{gs}	Gate-Source Charge		---	20	---	
Q_{gd}	Gate-Drain Charge		---	28	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=20V , V_{GS}=10V , R_G=1.5Ω, I_D=20A	---	38	---	ns
T_r	Rise Time		---	22	---	
$T_{d(off)}$	Turn-Off Delay Time		---	115	---	
T_f	Fall Time		---	150	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	7427	---	pF
C_{oss}	Output Capacitance		---	2930	---	
C_{rss}	Reverse Transfer Capacitance		---	538	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 inch[2] FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=41A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
6.Package limitation current is 85A.

Typical Characteristics
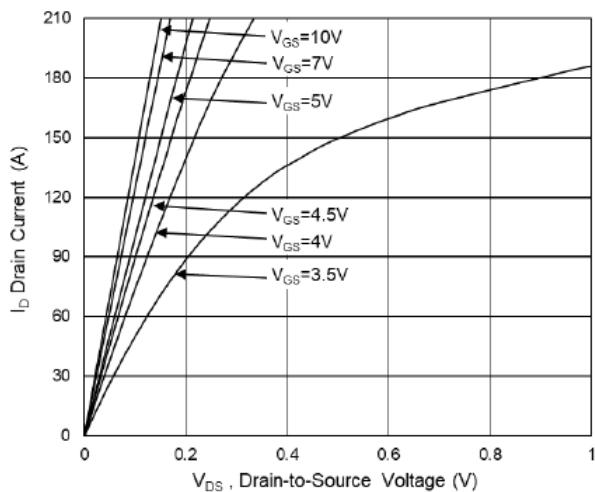

**Fig.1 Typical Output Characteristics**
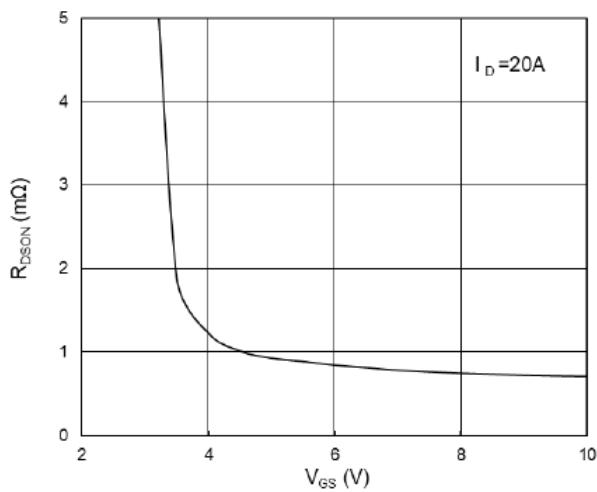
Fig.2 On-Resistance vs G-S Voltage
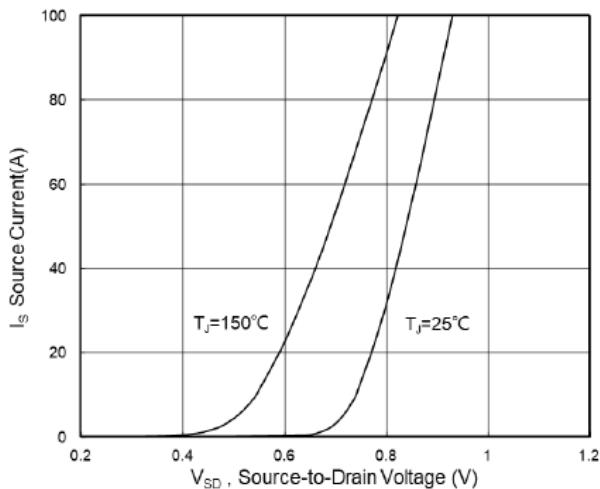
Fig.3 Source Drain Forward Characteristics
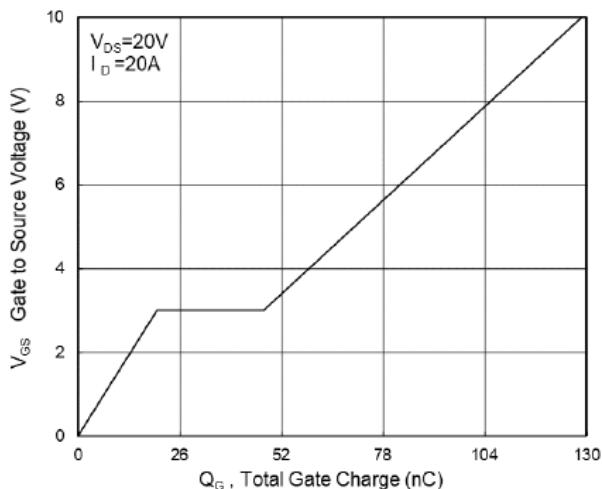
Fig.4 Gate-Charge Characteristics
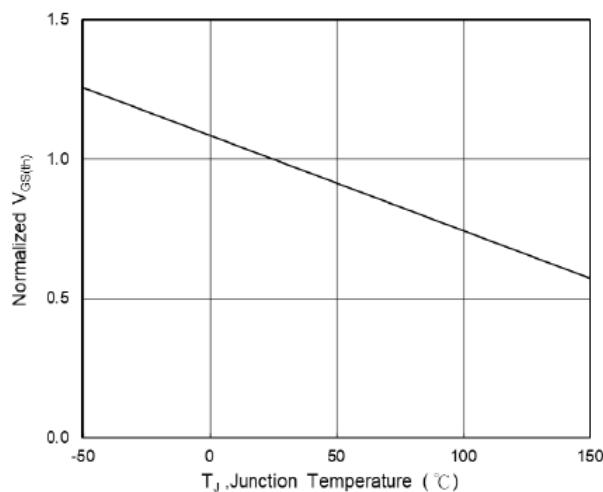
Fig.5 Normalized $V_{GS(th)}$ vs T_J
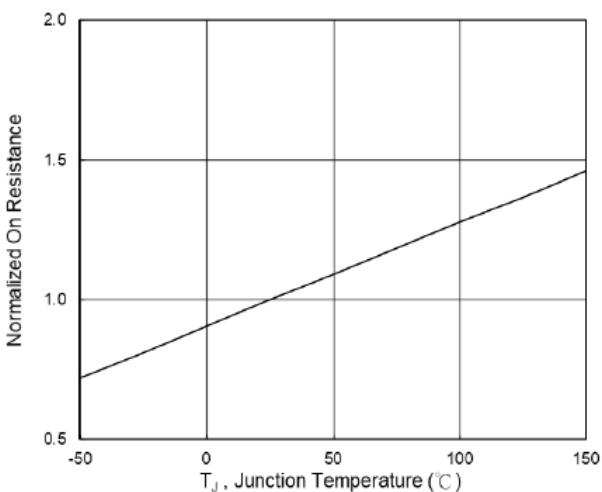
**Fig.6 Normalized R_{DSON} vs T_J**
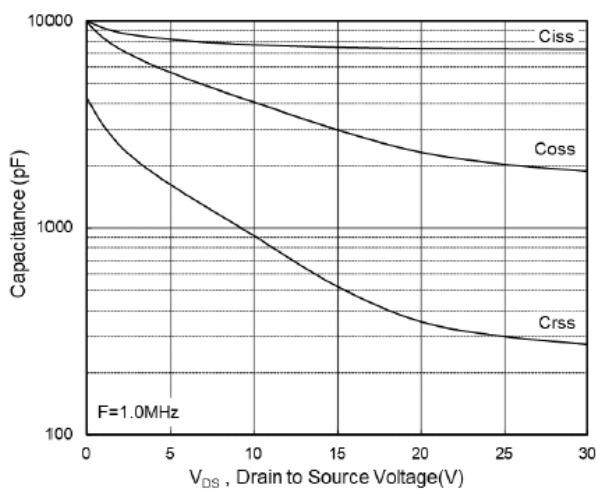
Fig.7 Capacitance
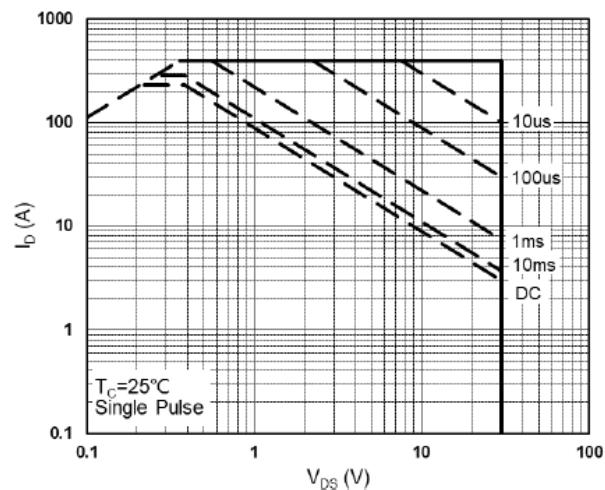
Fig.8 Safe Operating Area
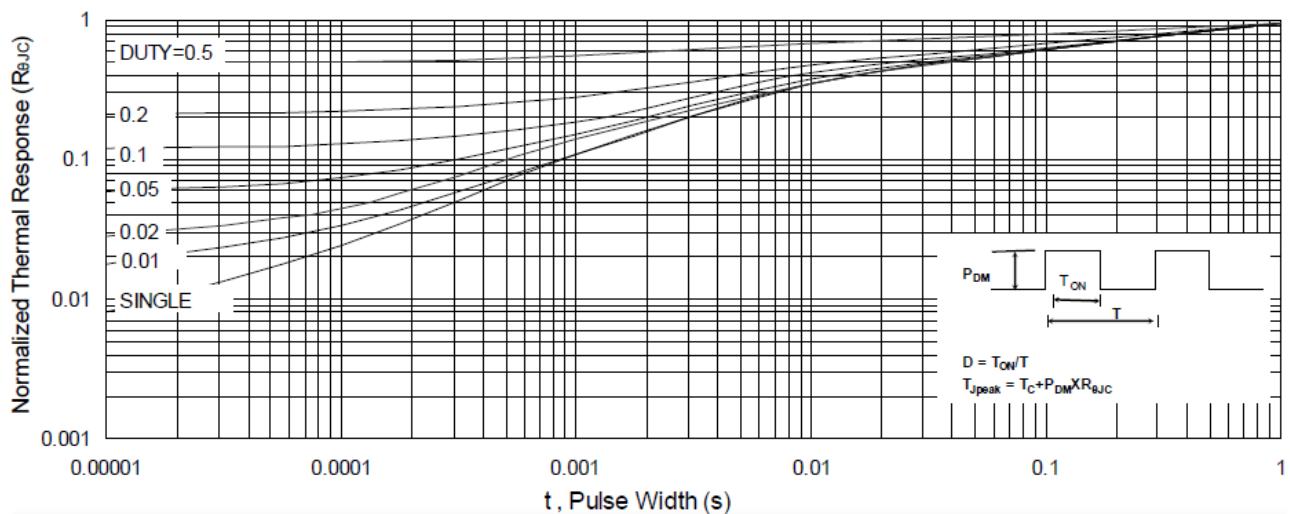
Fig.9 Normalized Maximum Transient Thermal Impedance
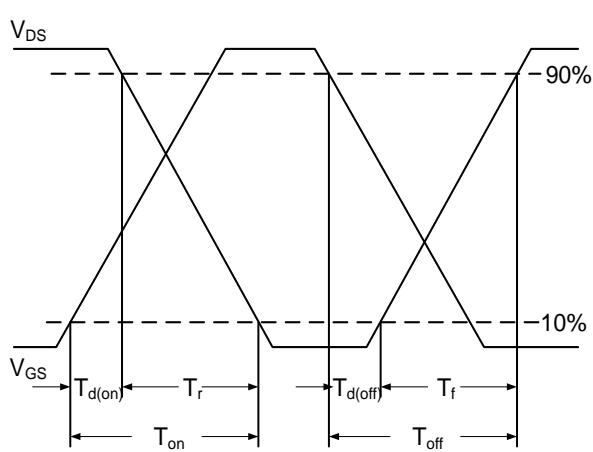
Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2}L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$
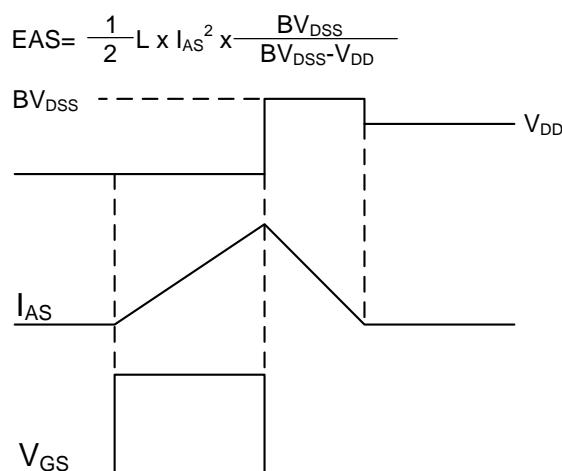
Fig.11 Unclamped Inductive Switching

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Ordering Information

Part Number	Package code	Packaging
HSBA3086	PRPAK5*6	3000/Tape&Reel

LAND PATTERN RECOMMENDATION
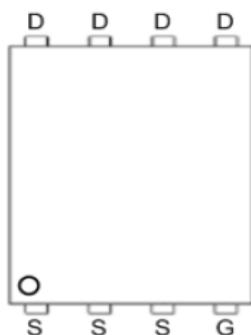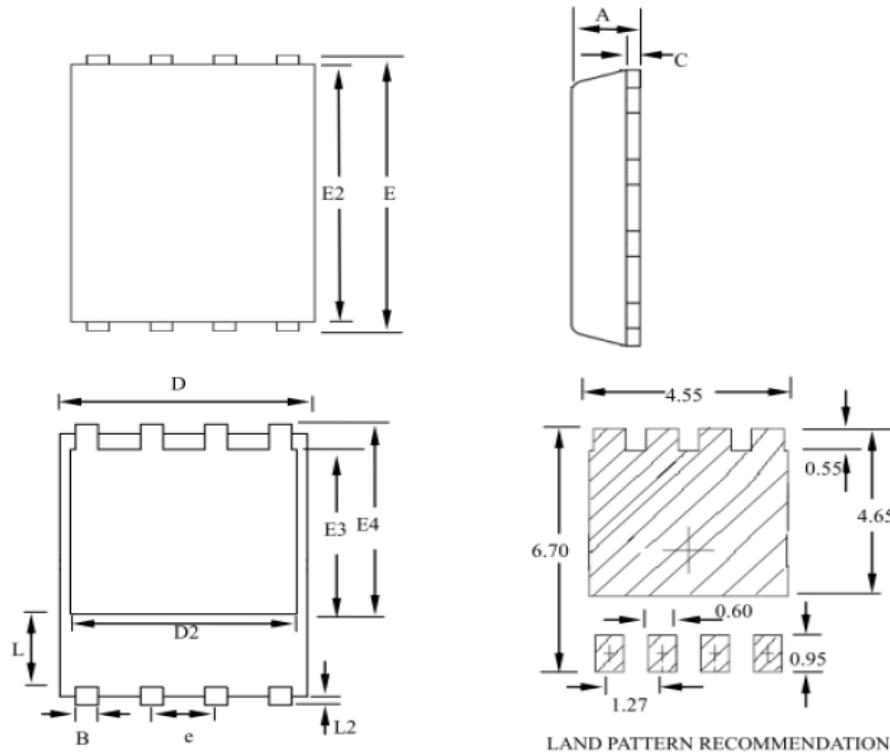
SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145		0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--

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